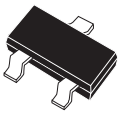
CMPD1001
CMPD1001A
CMPD1001S

HIGH CURRENT SWITCHING DIODE

Central™ Semiconductor Corp.



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPD1001 series types are silicon switching diodes manufactured by the epitaxial planar process, designed for applications requiring high current capability.

The following configurations are available:

CMPD1001	SINGLE	**MARKING CODE: L20**
CMPD1001S	DUAL, IN SERIES	**MARKING CODE: L21**
CMPD1001A	DUAL, COMMON ANODE	**MARKING CODE: L22**

MAXIMUM RATINGS (T_A=25°C)

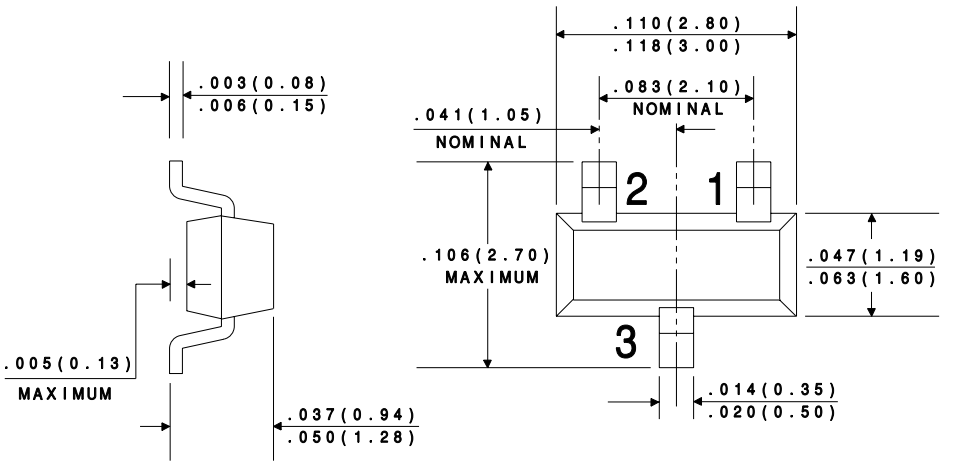
	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	90	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	600	mA
Peak Repetitive Reverse Current	I_{RRM}	600	mA
Forward Surge Current, tp=1 μs	I_{FSM}	6000	mA
Forward Surge Current, tp=1 s	I_{FSM}	1000	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

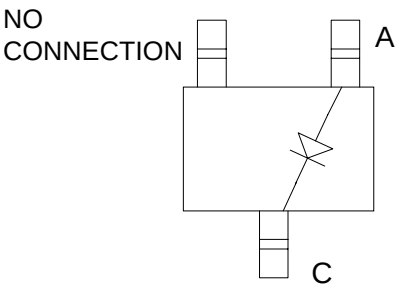
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
B_{VR}	I_R=100 μA	90		V
I_R	V_R=90V		100	nA
I_R	V_R=90V, T_A=150°C		100	μA
V_F	I_F=10mA		0.75	V

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
V_F	I_F=50mA		0.84	V
V_F	I_F=100mA		0.90	V
V_F	I_F=200mA		1.00	V
V_F	I_F=400mA		1.25	V
C_T	V_R=0, f=1 MHz		35	pF
t_{rr}	I_F=I_R=30mA, RECOV. TO 3.0mA, R_L=100Ω		50	ns

All dimensions in inches (mm).





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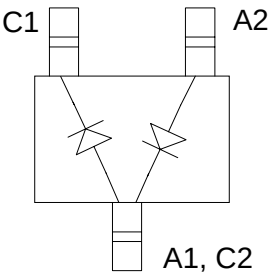
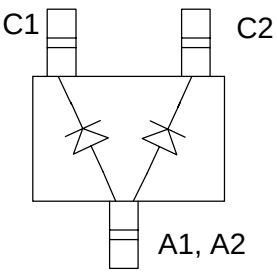


CMPD1001S



CMPD1001A

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